



**KERSEMI**

**AUTOMOTIVE GRADE**

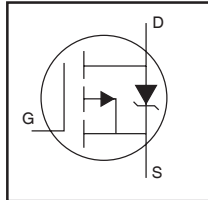
PD-96302

# AUIRFR6215

HEXFET® Power MOSFET

### Features

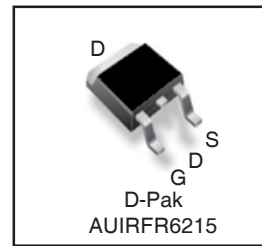
- P-Channel
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



$V_{(BR)DSS}$		<b>-150V</b>
$R_{DS(on)}$	<b>max.</b>	<b>0.295Ω</b>
$I_D$		<b>-13A</b>

### Description

Specifically designed for Automotive applications of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

### Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-13	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-9.0	
$I_{DM}$	Pulsed Drain Current ①⑥	-44	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally limited) ②⑥	310	mJ
$I_{AR}$	Avalanche Current ①⑥	-6.6	A
$E_{AR}$	Repetitive Avalanche Energy ①⑥	11	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

### Thermal Resistance

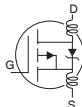
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥⑥	—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient(PCB mount)②	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

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## Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-150	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.20	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.295	$\Omega$	$V_{GS} = -10V, I_D = -6.6A$ ④
		—	—	0.58		$V_{GS} = -10V, I_D = -6.6A$ ④ $T_J = 150^\circ\text{C}$
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
gfs	Forward Transconductance	3.6	—	—	S	$V_{DS} = -50V, I_D = -6.6A$ ⑥
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-25	$\mu A$	$V_{DS} = -150V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

## Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	—	66	nC	$I_D = -6.6A$
$Q_{gs}$	Gate-to-Source Charge	—	—	8.1		$V_{DS} = -120V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	35		$V_{GS} = -10V$ , See Fig 6 and 13 ④⑥
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = -75V$
$t_r$	Rise Time	—	36	—		$I_D = -6.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	53	—		$R_G = 6.8\Omega$
$t_f$	Fall Time	—	37	—		$R_D = 12\Omega$ , See Fig. 10 ④⑥
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	860	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	220	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	130	—		$f = 1.0\text{MHz}$ , See Fig.5 ⑥

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-13	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑥	—	—	-44		
$V_{SD}$	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -6.6A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	160	240	ns	$T_J = 25^\circ\text{C}, I_F = -6.6A$
$Q_{rr}$	Reverse Recovery Charge	—	1.2	1.7	nC	$di/dt = 100A/\mu s$ ④⑥
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

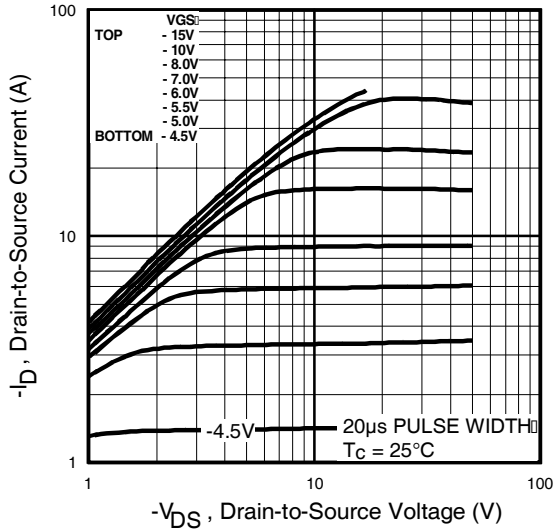


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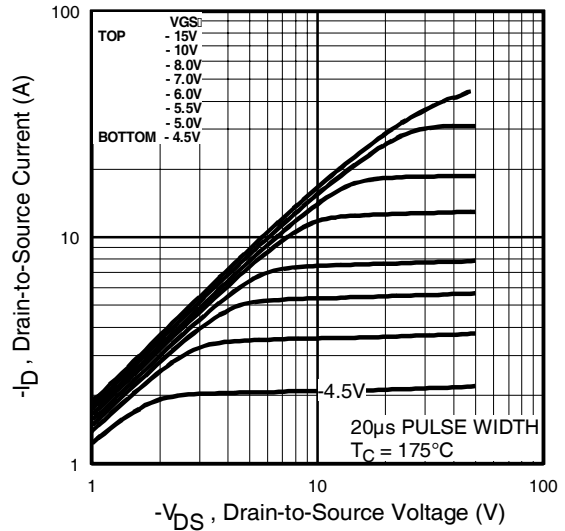
### Qualification Information<sup>†</sup>

<b>Qualification Level</b>		Automotive (per AEC-Q101) <sup>††</sup>	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		D PAK	MSL1
<b>ESD</b>	Machine Model	Class M4 AEC-Q101-002	
	Human Body Model	Class H3A AEC-Q101-001	
	Charged Device Model	Class C5 AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

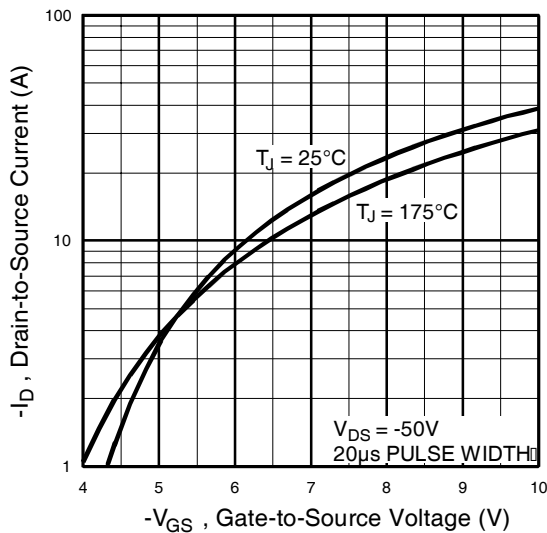
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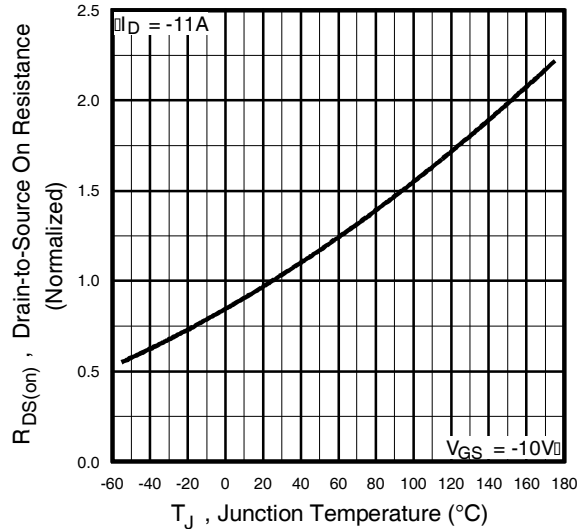
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



**Fig 3.** Typical Transfer Characteristics

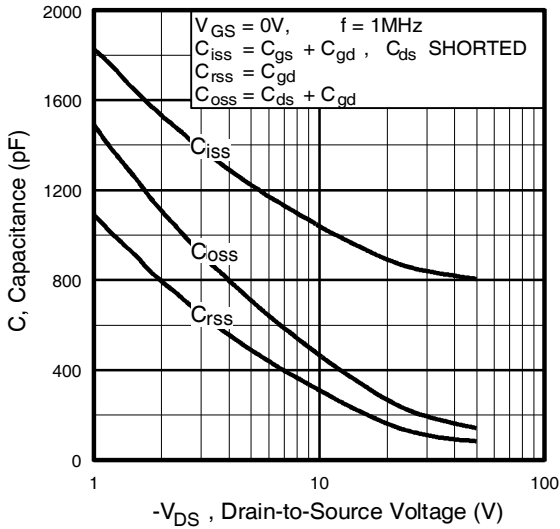


**Fig 4.** Normalized On-Resistance Vs. Temperature

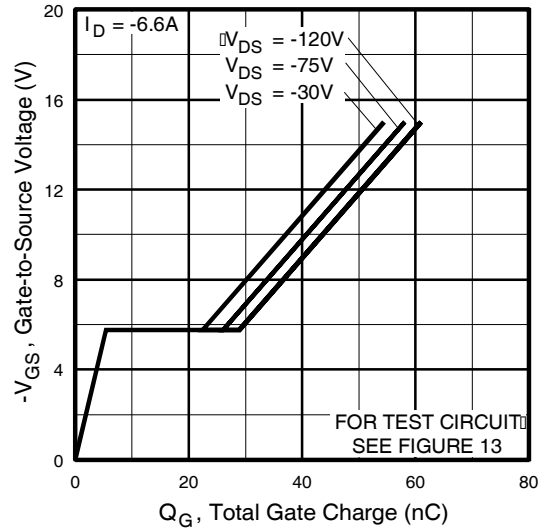


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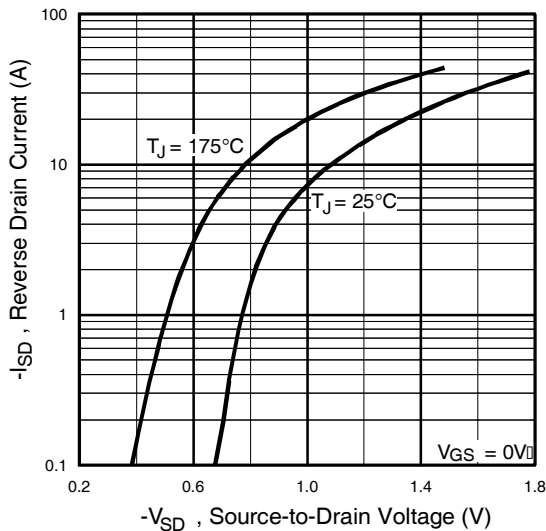
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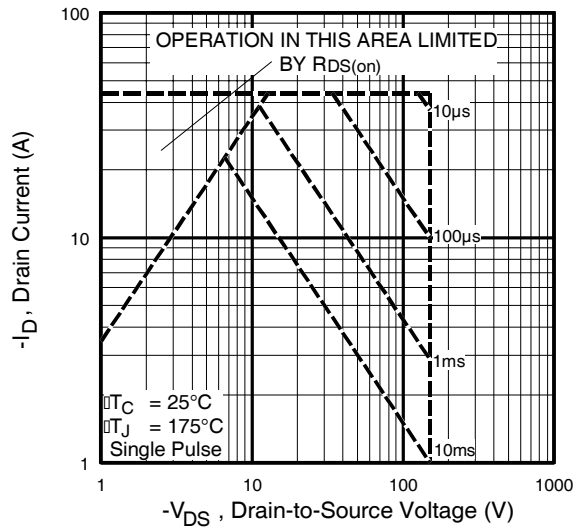
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

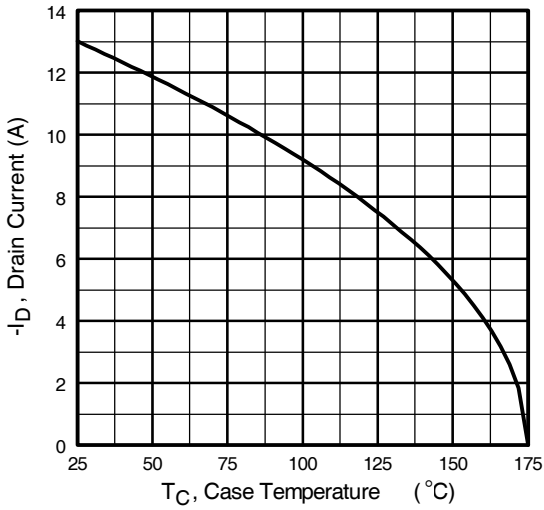


**Fig 7.** Typical Source-Drain Diode Forward Voltage

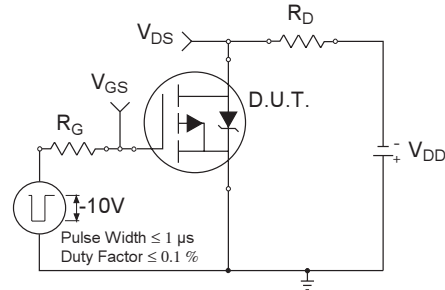


**Fig 8.** Maximum Safe Operating Area

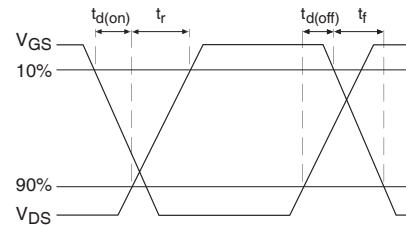
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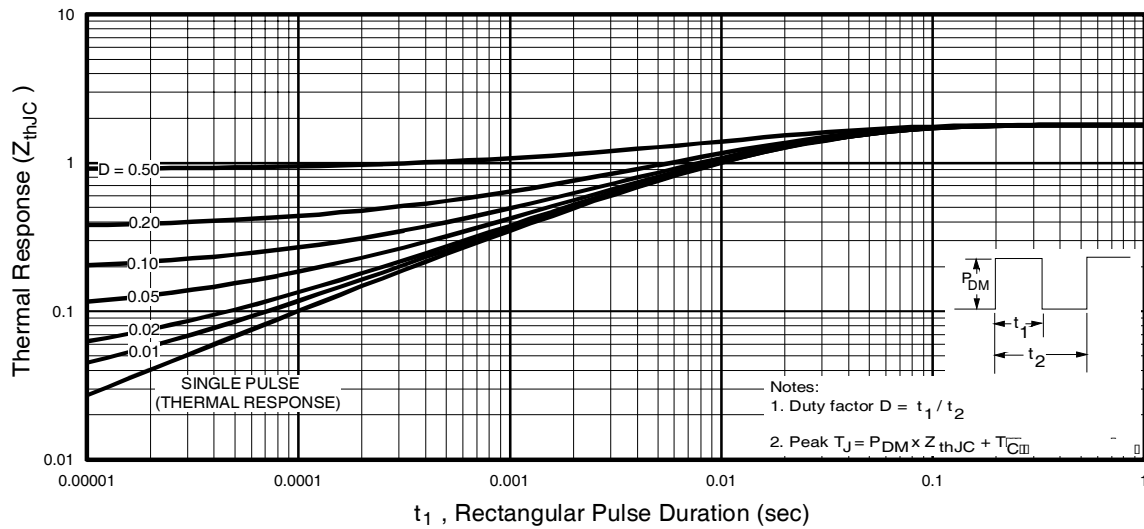
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

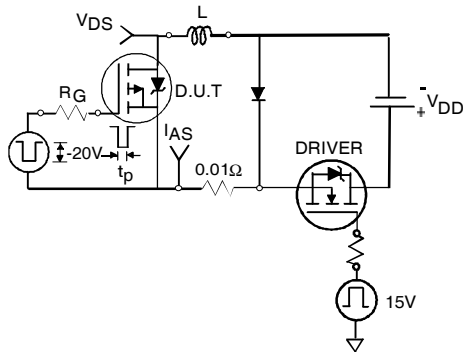


**Fig 10b.** Switching Time Waveforms

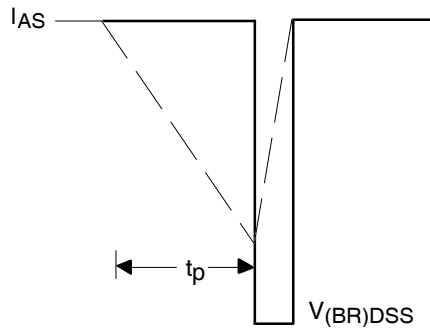


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

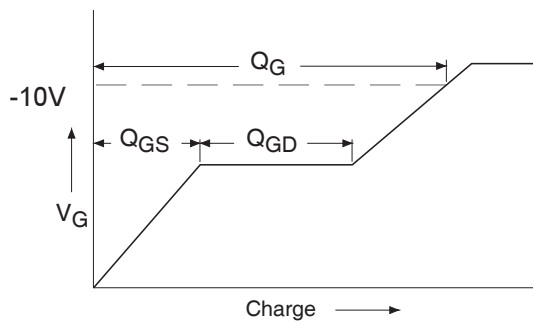
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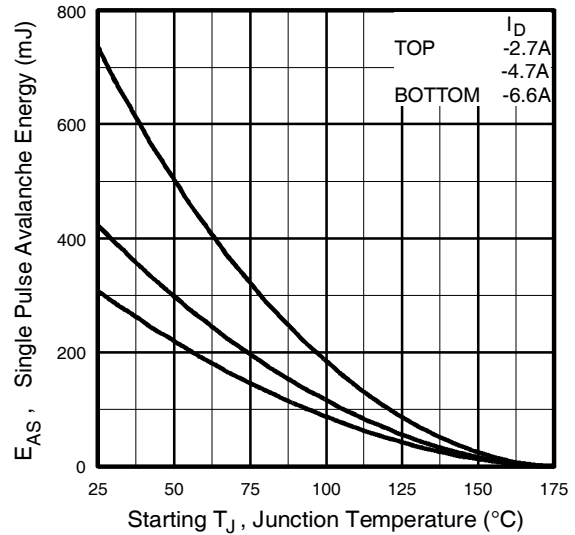
**Fig 12a.** Unclamped Inductive Test Circuit



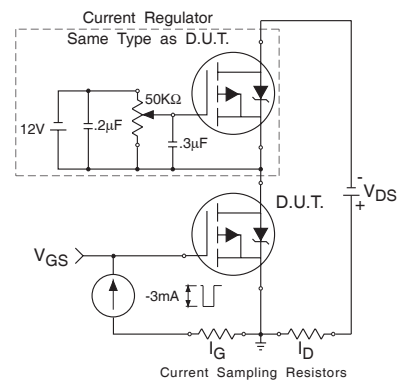
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



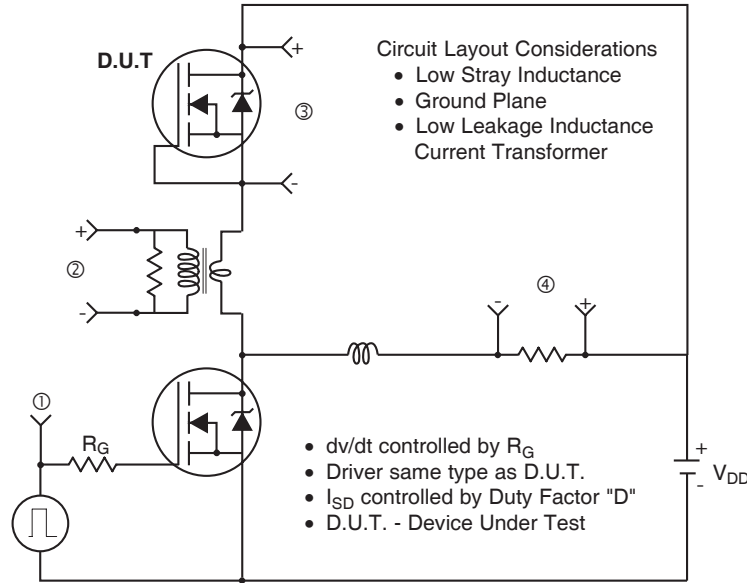
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



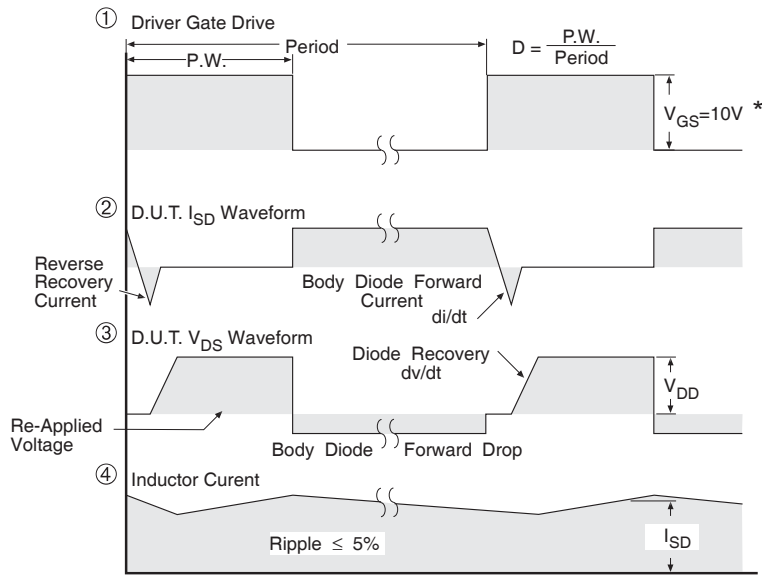
**Fig 13b.** Gate Charge Test Circuit

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## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFETS



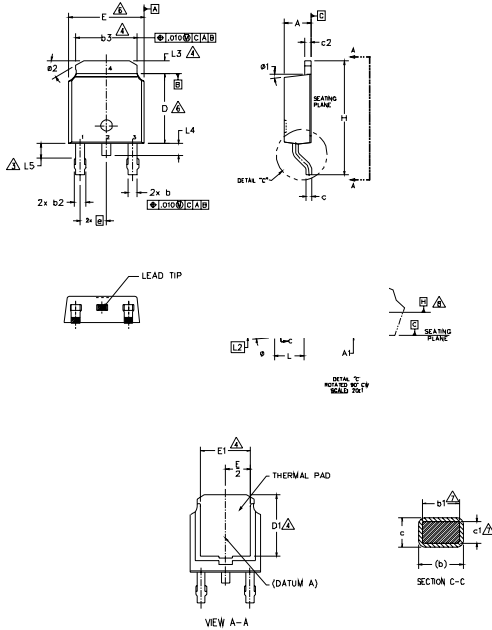


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## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  - 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
  - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
  - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
  - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.085	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

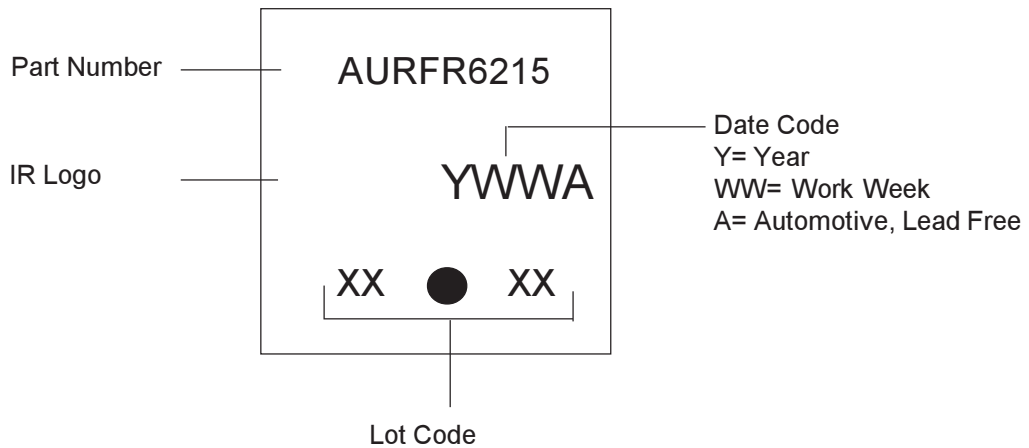
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

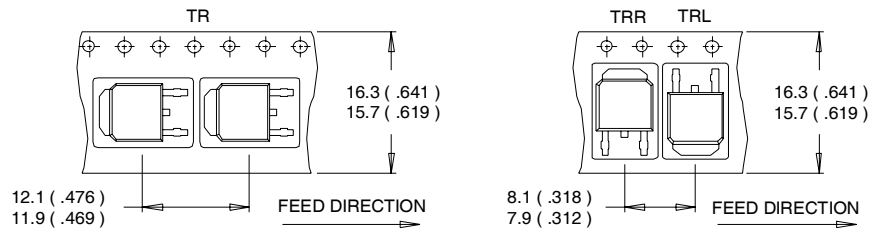
## D-Pak Part Marking Information



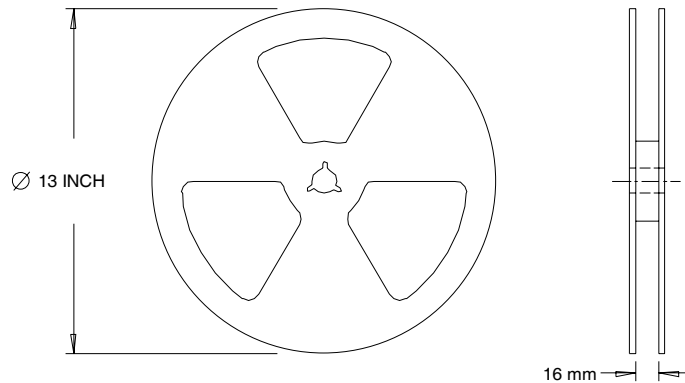
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## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 14\text{mH}$   $R_G = 25\Omega$ ,  $I_{AS} = -6.6\text{A}$ . (See Fig.12)
- ③  $I_{SD} \leq -6.6\text{A}$ ,  $di/dt \leq -620\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
- ⑤ This is applied for I-PAK,  $L_S$  of D-PAK is measured between lead and center of die contact
- ⑥ Uses IRF6215 data and test conditions
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material ) For recommended footprint and soldering techniques refer to application note #AN-994
- ⑧  $R_{\theta}$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .